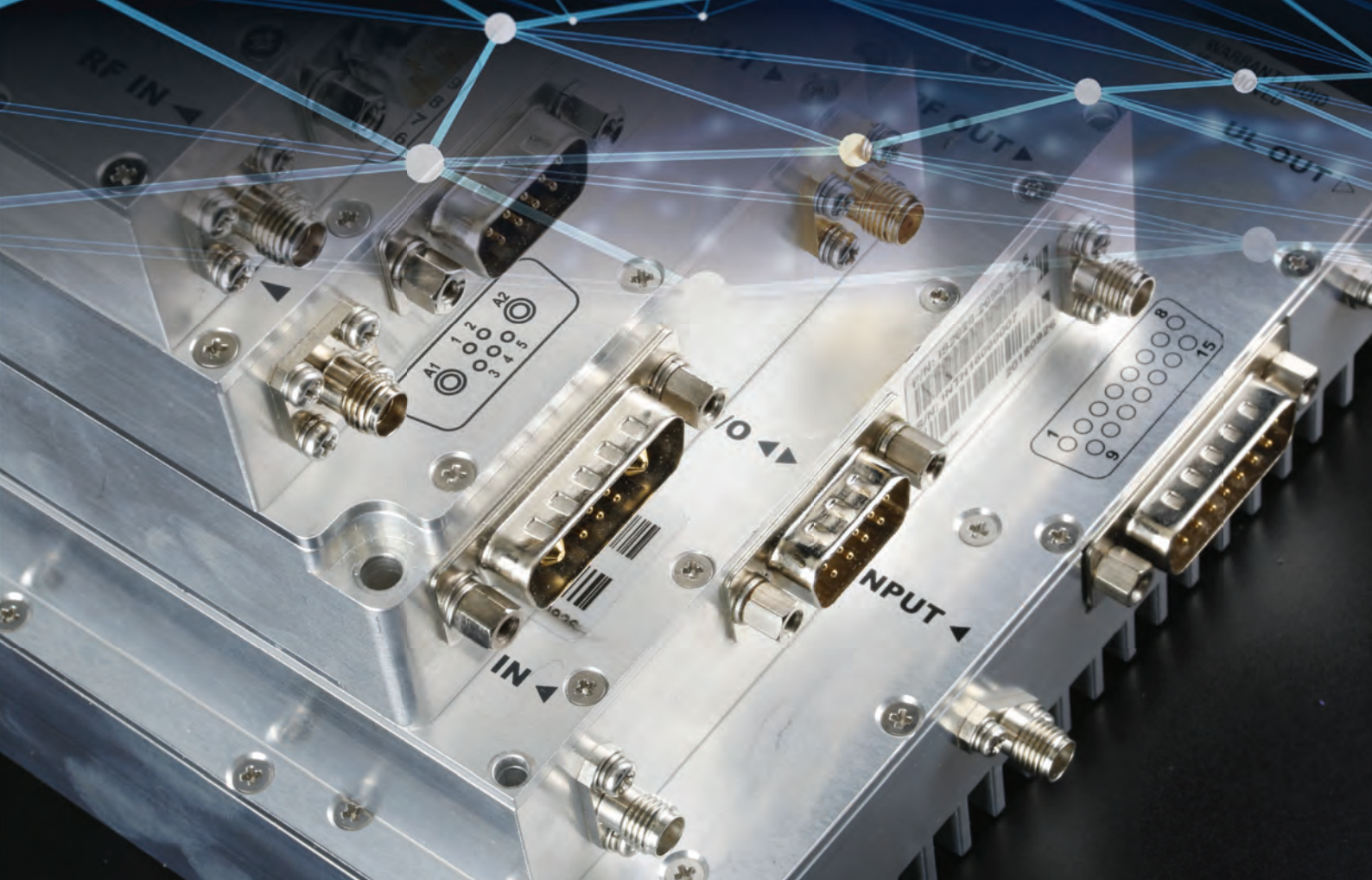


INSPOWER™

Cellular Power Amplifier
Broadband GaN Power Amplifier
Amplifier System



PRODUCT

Cellular Power Amplifiers



Inpower's Cellular Power Amplifiers are ideal for customers involved with DAS systems, BTS solutions and RF repeaters, which require highly linear products with low distortion and low EVM. They are well-suited for LTE, Cellular, WCDMA, GSM, PCS and UMTS systems. These products are been designed in combination with various technologies, symmetrical and asymmetrical Doherty configurations to achieve high efficiency, and feed-forward, analog pre-distortion and other linearization techniques to achieve high linearity. These Products are used by leading global DAS manufacturers and mobile network companies.

Model Number	Frequency Start(MHz)	Frequency Stop(MHz)	Linear Pout(Watt)	Linear Pout(dBm)	Gain (dB)	Voltage (Volts)	Current (Amps)	Two-tone IMD(dBm)	Size (mm)	Application
ILA1044	462	468	30	45	45	48	3.6	-	140 x 150 x 25.4	LTE Band 31
ILA1037	617	652	2.5	34	41	28	1.1	-20	120 x 110 x 25	LTE 600
ILA1057	617	652	60	48	50	28	8	-	175 x 150 x 25	LTE 600
ILA1001	728	757	2.5	34	41	28	1.1	-20	120 x 110 x 25	LTE 700
ILA1018	752.5	762.5	20	43	46	28	5	-12	173 x 108 x 25.4	QAM
ILA1002	758	803	2.5	34	41	28	1.1	-18	120 x 110 x 25	LTE 700
ILA1040	758	803	30	45	45	28	3.5	-	120 x 150 x 28	LTE 700
ILA1003	791	821	2.5	34	41	28	1.1	-20	120 x 110 x 25	LTE 800
ILA1043	859	894	30	45	45	28	3.5	-	120 x 150 x 28	LTE 800
ILA1004	862	894	2.0	33	41	28	1.1	-20	120 x 110 x 25	Cellular/LTE
ILA1005	925	960	2.0	33	41	28	1.4	-38	130 x 120 x 30	EGSM
ILA1006	1805	1880	3.5	35.5	43	28	1.6	-32	130 x 120 x 30	DCS
ILA1007	1930	2000	3.5	35.5	43	28	1.45	-20	120 x 110 x 30	PCS/LTE
ILA1026	2110	2180	3.5	35.5	43	28	1.4	-15	130 x 120 x 25	UMTS/AWS
ILA1021	2110	2180	25	44	52	28	5	-	170 x 145 x 25	UMTS/AWS
ILA1048	2110	2170	60	48	48	28	10	-	230 x 220 x 28	UMTS/AWS
ILA1038	2300	2400	10	40	44	28	2.5	-	170 x 150 x 35	LTE 2400-TDD
ILA1009	2345	2360	4.0	36	45	28	1.4	-20	120 x 110 x 25	WCS
ILA1011	2496	2690	5.0	37	45	28	1.6	-15	170 x 150 x 35	LTE TDD
ILA1030	2496	2690	20	43	60	28	5	-	170 x 145 x 25	LTE TDD
ILA1049	2496	2690	60	48	48	28	10	-	230 x 220 x 28	LTE TDD
ILA1010	2620	2690	3.5	35.5	45	28	1.4	-15	120 x 110 x 25	LTE 2600
ILA1047	3800	4100	1	30	45	28	1.2	-	180 x 160 x 28	5G NR
ILA1045	3300	3800	10	40	40	28	4	-	170 x 150 x 35	5G NR

Band Specific Amplifiers



Band Specific Amplifiers are the best solution to reduce cost and improve linearity and efficiency performance over a narrower frequency range than broadband amplifiers. Although designed with LDMOS, GaN and GaAs FET, LDMOS FET has a priority to optimize cost and performance. Output isolator can also be installed.

Model Number	Frequency Start(MHz)	Frequency Stop(MHz)	Pout (Watts)	Gain (dB)	Voltage (Volts)	Current (Amps)	Size (mm)	Device Type
INS2080	430	470	12.5	42	28	1.5	110 x 90 x 22	LDMOS
INS2008	600	800	25	44	28	3	150 x 90 x 25	LDMOS
INS2076	720	960	25	45	28	3.7	110 x 90 x 22	LDMOS
INS2074	800	1000	15	43	28	3	110 x 90 x 22	LDMOS
INS2001	800	1000	50	48	27	5.5	110 x 95 x 22	LDMOS
INS2017	860	960	100	50	27	12	140 x 125 x 25	LDMOS
INS2032	900	1300	80	49	28	10	200 x 90 x 28	GaN
INS2071	1200	1400	50	48	28	6	162.5 x 86.4 x 25.4	LDMOS
INS2009	1500	1700	50	49	24	5.5	110 x 95 x 22	LDMOS
INS2075	1700	2000	25	45	28	4	110 x 90 x 22	LDMOS
INS2002	1800	2000	50	48	27	5.5	110 x 95 x 22	LDMOS
INS2004	1800	2000	100	50	27	12	150 x 135 x 25	LDMOS
INS2077	1800	2170	25	45	28	3.7	110 x 90 x 22	LDMOS
INS2010	2100	2300	50	48	27	5.5	110 x 95 x 22	LDMOS
INS2078	2400	2500	15	43	28	3	110 x 90 x 22	LDMOS
INS2079	2400	2700	25	45	28	4	110 x 90 x 22	LDMOS
INS2006	3400	3600	4	19	7	3	71.12 x 38.1 x 13.97	GaAs
INS2007	3400	3600	15	46	28	4	200 x 150 x 37	LDMOS
INS2018	3400	3600	40	51	28	8.5	200 x 150 x 37	LDMOS
INS2005	3400	3700	100	58	28	22	150 x 170 x 28	LDMOS
INS2028	4400	5000	3	34	12	1.5	90 x 90 x 20	GaN
INS2012	4400	5000	20	46	28	2.5	156 x 82 x 20	GaN
INS2102	5000	6000	100	50	28	20	285 x 125 x 25	GaN

Broadband Amplifiers



Inspower's Broadband amplifiers are available in frequencies between 1 MHz and 8GHz with power levels up to 200Watts. Using the latest solid-state technologies such as GaN, LDMOS and GaAs, our expert engineers cater to a wide range product lines. The Table below shows some of the popular models that we have already developed. And the models is being still extended and upgraded by continuous R&D Activities to satisfy customer requirements.

Model Number	Frequency Start(MHz)	Frequency Stop(MHz)	Pout (Watts)	Gain (dB)	Voltage (Volts)	Current (Amps)	Size (mm)	FWD Detector	Device Type
INS3001	1	100	50	46	28	7	162.56 x 86.4 x 25.4		LDMOS
INS3098	20	520	50	48	28	9	162.56 x 86.4 x 25.4		LDMOS
INS3024	20	520	100	50	28	12	134.62 x 63.5 x 26.67		LDMOS
INS3004	20	530	12	42	28	1	85 x 85 x 26	O	GaN
INS3018	20	530	100	50	28	8.5	185 x 80 x 27	O	LDMOS
INS3005	20	1000	100	58	28	9	162.56 x 86.36 x 27		GaN
INS3012	800	2170	12	42	28	2.5	170 x 70 x 22		GaN
INS3045	20	2500	10	40	24	2.1	100 x 85 x 20		GaN
INS3006	500	2500	50	46	28	6	200 x 90 x 28	O	GaN
INS3035	500	2500	100	50	28	12	185 x 90 x 22		GaN
INS3008	500	2500	100	49	28	14	200 x 140 x 27	O	GaN
INS3037	700	2700	100	50	28	14	185 x 90 x 22		GaN
INS3020	1000	3000	50	40	28	7	170 x 70 x 30		GaN
INS3026	2500	6000	35	46	28	10	185 x 90 x 20		GaN
INS3078	3000	6000	35	46	28	9	170 x 70 x 30		GaN
INS3091	2000	5000	50	47	28	10	185 x 90 x 20		GaN
INS3072	2000	6000	100	50	28	24	230 x 120 x 25		GaN

Amplifier Systems



Inspower designs and manufactures High Power RF and Microwave Systems for use in test & measurement, communications and other types of systems. The systems we make typically contain high power amplifiers, heat sink / fan, power supply and Breaker / switch. Options can include voltage variable attenuators, circulators, forward / reflected ports and other controls and monitoring.

Model Number	Frequency Start(MHz)	Frequency Stop(MHz)	Pout (Watts)	Gain (dB)	Voltage (VAC)	Pd (Watts)	Size (inch)	Device Type
INS5032	20	520	100	50	100-240	850	R2U	LDMOS
INS5028	500	2500	50	46	100-240	500	R2U	GaN
INS5035	500	2500	100	50	100-240	800	R2U	GaN
INS5037	700	2700	100	50	100-240	800	R2U	GaN
INS5029	1000	3000	50	47	100-240	500	R2U	GaN
INS5005	1000	3000	100	50	100-240	800	R2U	GaN
INS5007	2500	6000	35	48	100-240	500	R2U	GaN
INS5039	2000	6000	50	47	100-240	500	R2U	GaN
INS5040	2000	6000	100	50	100-240	1200	R3U	GaN

5G Power Amplifiers

Broadband GaN Power Amplifiers

Amplifier Systems



INSPOWER™

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